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FCP9N60N / FCPF9N60NT N-Channel SupreMOS[®] MOSFET

600 V, 9 A, 385 mΩ

Features

- R_{DS(on)} = 330 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 4.5 A
- Ultra Low Gate Charge (Typ. Q_q = 22 nC)
- Low Effective Output Capacitance (Typ. Coss(eff.) = 106 pF)
- 100% Avalanche Tested
- · RoHS Compliant

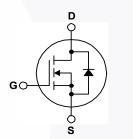
Application

- LCD/LED/PDP TV
- Lighting
- · Solar Inverter
- AC-DC Power Supply

Description

The SupreMOS® MOSFET is Fairchild Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest Rsp on-resistance, superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.





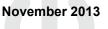
Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

	Parameter	FCP9N60N	FCPF9N60NT	Unit		
Drain to Source Voltage			6	V		
Gate to Source Voltage			±	V		
Drain Current	- Continuous (T _C = 25 ^o C)	- Continuous (T _C = 25 ^o C)		9.0 9.0*		
Drain Current	- Continuous (T _C = 100 ^o C)		5.7	5.7*	A	
Drain Current	- Pulsed	(Note 1)	27 27*		А	
Single Pulsed Avalanche E	1	mJ				
Avalanche Current			3		А	
Repetitive Avalanche Energy (0.83		mJ	
MOSFET dv/dt			100		V/ns	
Peak Diode Recovery dv/dt			20		V/ns	
Dower Dissinction	(T _C = 25°C)		83.3	29.8	W	
Power Dissipation	- Derate Above 25°C		0.67	0.24	W/ºC	
Operating and Storage Temperature Range			-55 to	°C		
Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds 300			00	°C		
	Gate to Source Voltage Drain Current Drain Current Single Pulsed Avalanche E Avalanche Current Repetitive Avalanche Energ MOSFET dv/dt Peak Diode Recovery dv/dt Power Dissipation Operating and Storage Terr	$\begin{array}{l} \mbox{Drain to Source Voltage} \\ \hline \mbox{Gate to Source Voltage} \\ \hline \mbox{Gate to Source Voltage} \\ \hline \mbox{Gate to Source Voltage} \\ \hline \mbox{Drain Current} & - Continuous (T_C = 25^{\circ}C) \\ \hline \mbox{- Continuous (T_C = 100^{\circ}C)} \\ \hline \mbox{- Continuous (T_C = 100^{\circ}C)} \\ \hline \mbox{Drain Current} & - Pulsed \\ \hline \mbox{Single Pulsed Avalanche Energy} \\ \hline \mbox{Avalanche Current} \\ \hline \mbox{Repetitive Avalanche Energy} \\ \hline \mbox{MOSFET dv/dt} \\ \hline \mbox{Peak Diode Recovery dv/dt} \\ \hline \mbox{Power Dissipation} & \frac{(T_C = 25^{\circ}C)}{- Derate Above 25^{\circ}C} \\ \hline \hline \\ \hline \mbox{Operating and Storage Temperature Range} \\ \hline \end{array}$	$\begin{array}{c} \mbox{Drain to Source Voltage} \\ \hline Gate to Source Voltage \\ \hline Orain Current & - Continuous (T_C = 25^{\circ}C) \\ \hline - Continuous (T_C = 100^{\circ}C) \\ \hline - Continuous (T_C = 100^{\circ}C) \\ \hline - Continuous (T_C = 100^{\circ}C) \\ \hline Other Other (Note 1) \\ \hline Other Other (Note 2) \\ \hline Other Other (Note 3) \\ \hline Oth$	$\begin{array}{c c} \mbox{Drain to Source Voltage} & \mbox{Gate to Source Voltage} & \mbox{fc} = 25^{\circ}{\rm C}) & \mbox{9.0} & \mbox{fc} = 25^{\circ}{\rm C}) & \mbox{fc} = 100^{\circ}{\rm C}) & \mbox{5.7} & \mbox{fc} = 100^{\circ}{\rm C}) & \mbox{5.7} & \mbox{fc} = 100^{\circ}{\rm C}) & \mbox{5.7} & \mbox{fc} = 100^{\circ}{\rm C}) & \mbox{fc} = 100^{\circ}{\rm C}) & \mbox{fc} = 100^{\circ}{\rm C}) & \mbox{fc} = 100^{\circ}{\rm C} & \mbox{fc} = 10^{\circ}{\rm C} & \mbox{fc} = $	$\begin{array}{c c c c c c c } \mbox{Drain to Source Voltage} & & & & & & & & & & & & & & & & & & &$	

Drain current limited by maximum junction temperature.

Thermal Characteristics

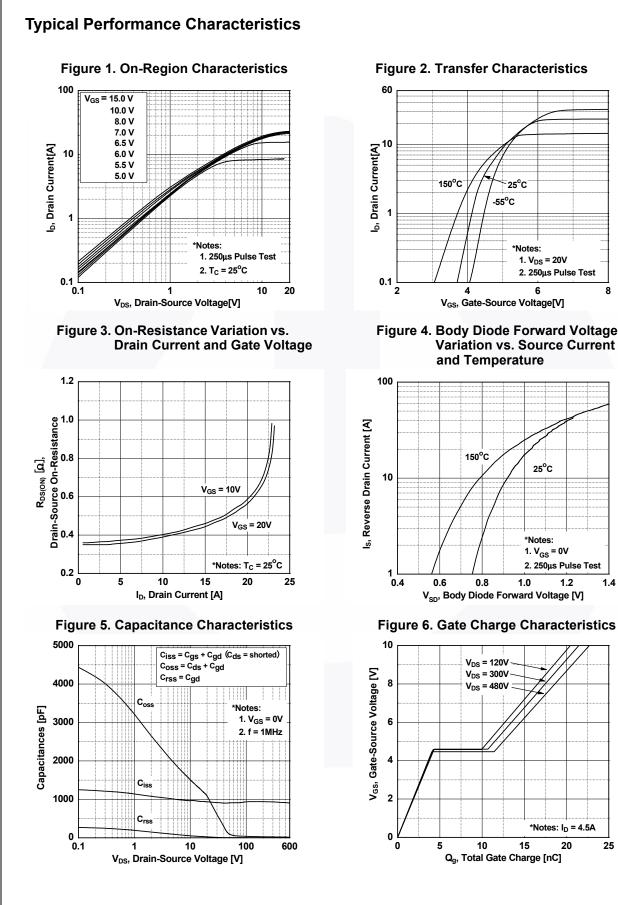
Symbol	Parameter	FCP9N60N	FCPF9N60NT	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	1.5	4.2	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	0/00



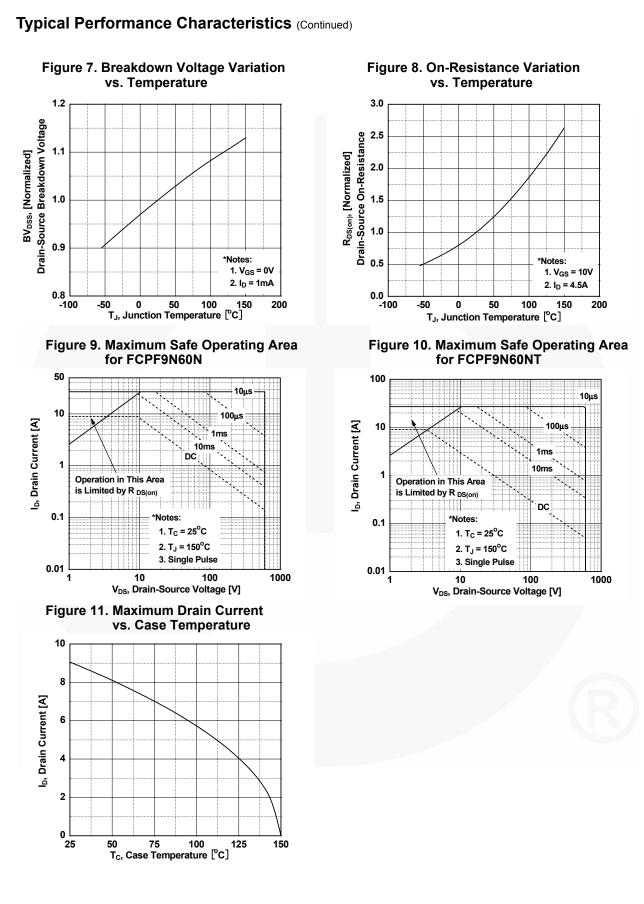
		Packag	-	Method	Reel Size	Tape Width		Quantity		
FCP9N6		FCP9N60N	TO-22			N/A		N/A	50 units	
			TO-220	220F Tube N/A				N/A	50 units	
	I Chara	Parameter	25ºC unless				Min	Turn	Max	Unit
Symbol	toriotio			Test	Condition	15	Min.	Тур.	Max.	Unit
Dff Charac _{3V_{DSS}}	-	Source Breakdown Vo	Itane	$l_{\rm p} = 1 \text{mA} \text{V}_{\rm p}$	$= 0 V T_{0}$	= 25 ⁰ C	600	-	-	V
∆BV _{DSS}		wn Voltage Temperatu	0		$V_{GS} = 0 V, T_C = 25^{\circ}C$		000			
/ΔTJ		Coefficient		I _D = 1 mA, Re	erenced to	0 25℃	-	0.72	-	V/ºC
I _{DSS}	Zero Ga	Zero Gate Voltage Drain Current		V _{DS} = 480 V, V			-	-	10	μA
				V_{DS} = 480 V, V_{GS} = 0 V, T_{C} = 125°C			-	-	100	μι
GSS	Gate to	Body Leakage Current		V_{GS} = ±30 V, V	V _{DS} = 0 V		-	-	±100	nA
On Charac	teristics	3								
V _{GS(th)}	Gate Th	reshold Voltage		$V_{GS} = V_{DS}, I_{D}$	= 250 μA		2.0	-	4.0	V
R _{DS(on)}		rain to Source On Resis	stance	V _{GS} = 10 V, I _C			-	0.33	0.385	Ω
9 _{FS}	Forward	Transconductance		V _{DS} = 40 V, I _D	= 4.5 A		-	7.5	1	S
Dynamic C	haracte	ristics								
C _{iss}		pacitance	_		-		<u> </u>	930	1240	pF
C _{oss}		Capacitance		V _{DS} = 100 V,	V _{GS} = 0 V,			35	50	pF
C _{rss}		everse Transfer Capacitance		f = 1 MHz			-	2	4	pF
C _{oss}		Capacitance	-	V _{DS} = 380 V,	$V_{CS} = 0 V$	f = 1 MHz		20	-	pF
C _{oss(eff.)}		Output Capacitance		$V_{DS} = 0 V \text{ to } 4$				106	-	pF
Q _{g(tot)}		te Charge at 10V		$V_{\rm DS} = 380 \rm V,$		•••	-	22.0	29	nC
Q _{gs}		Source Gate Charge		$V_{\rm DS} = 360 \text{ V},$ $V_{\rm GS} = 10 \text{ V}$	D - 4.5 A,		-	4.1	-	nC
Q _{gd}		Drain "Miller" Charge				(Note 4)	-	7.1	-	nC
ESR	Equivale	ent Series Resistance (G-S)	f = 1 MHz				2.9		Ω
Switching	Charact	eristics								
	1	Delay Time						12.7	35.4	ns
t _{d(on)} t _r		Rise Time		V _{DD} = 380 V, I _D = 4		= 4.5 A,		8.7	27.4	ns
t _{d(off)}		rn-Off Delay Time		$V_{GS} = 10 \text{ V}, \text{ R}_{G} = 4.7 \Omega$ (Note 4)			-	36.9	83.8	ns
t _f	Turn-Off Fall Time							10.2	30.4	ns
		le Characteristics								
I _s	-	n Continuous Drain to S		le Forward Curre	ant		-	-	9.0	А
s sм		n Pulsed Drain to Sour					-	- /	27	A
V _{SD}		Source Diode Forward		V _{GS} = 0 V, I _{SD}	= 4.5 A		-		1.2	V
t _{rr}		Recovery Time		$V_{GS} = 0 V, I_{SD}$			-	213	-	ns
Q _{rr}		Recovery Charge		$dI_{F}/dt = 100 \text{ A}/\mu\text{s}$		-	2.2	·	μC	
. I _{AS} = 3 A, R _G = 2 . I _{SD} ≤ 9 A, di/dt ≤	25 Ω, starting 200 A/μs, V _D	imited by maximum junction tert $T_J = 25^{\circ}$ C. $_D = 380$ V, starting $T_J = 25^{\circ}$ C. rating temperature typical chains								

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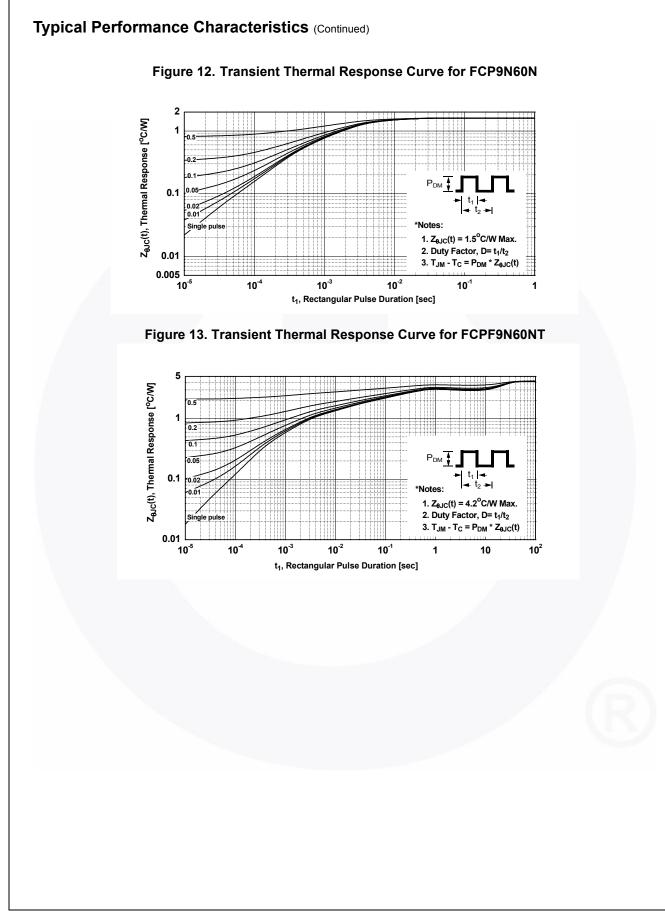
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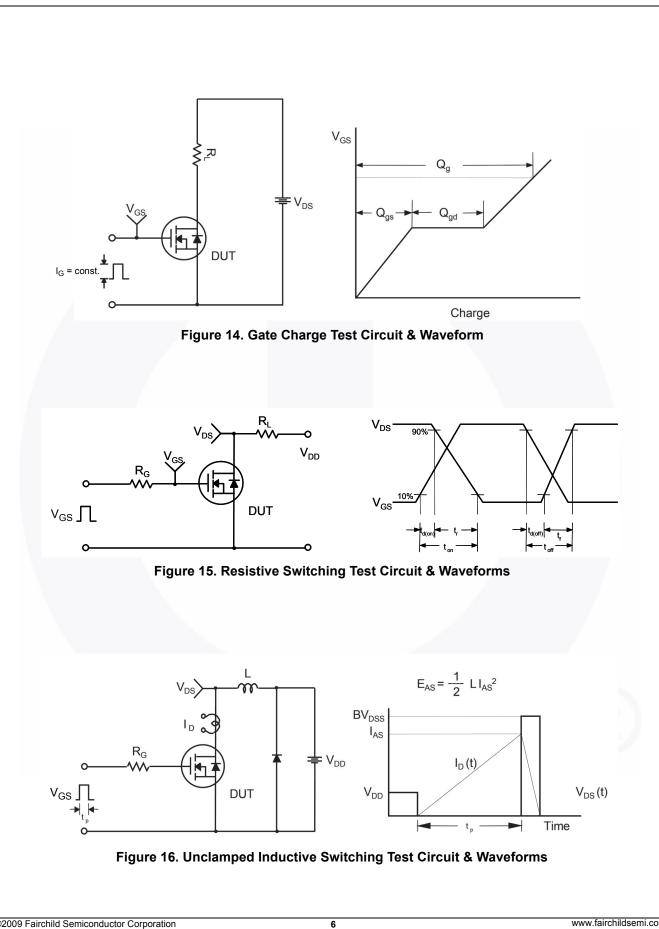
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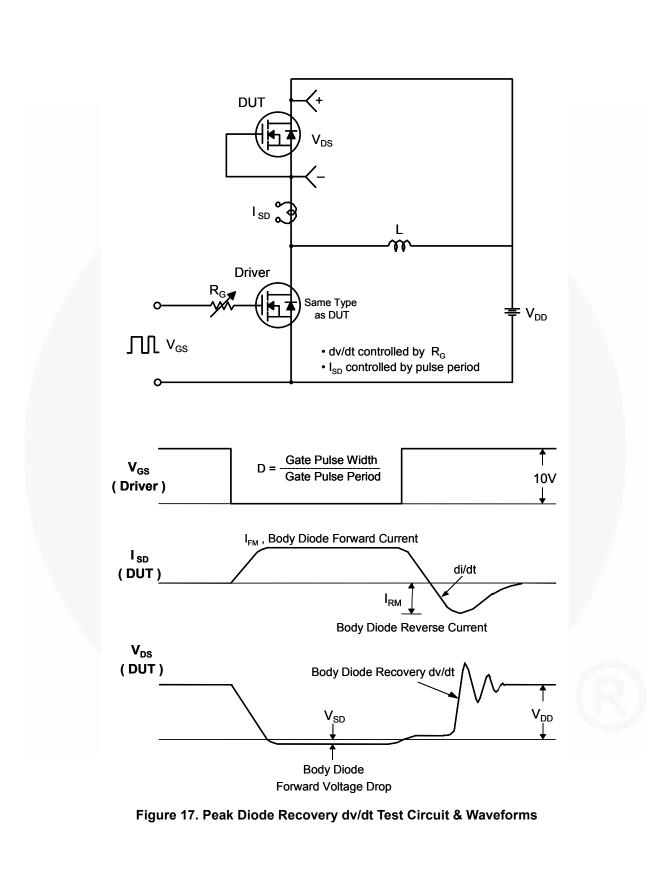
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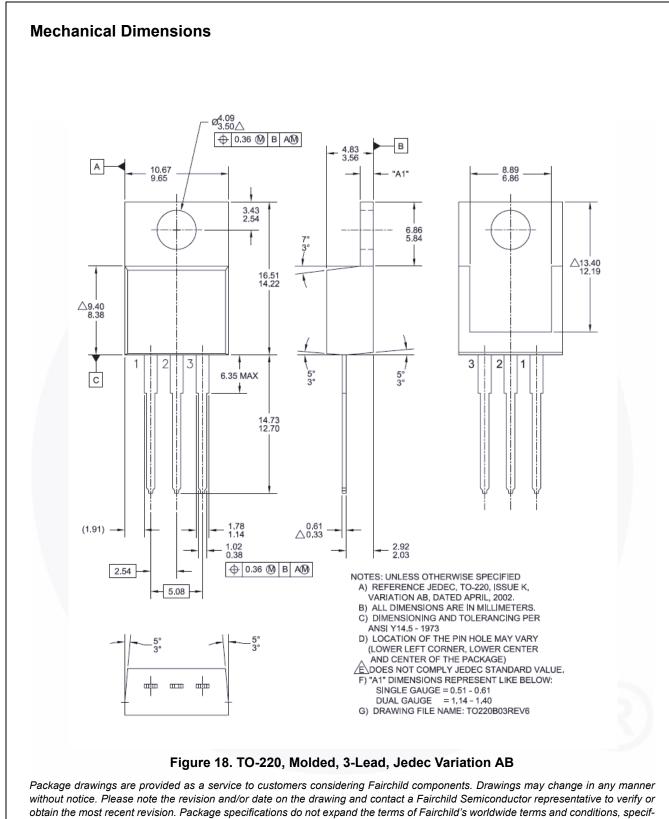


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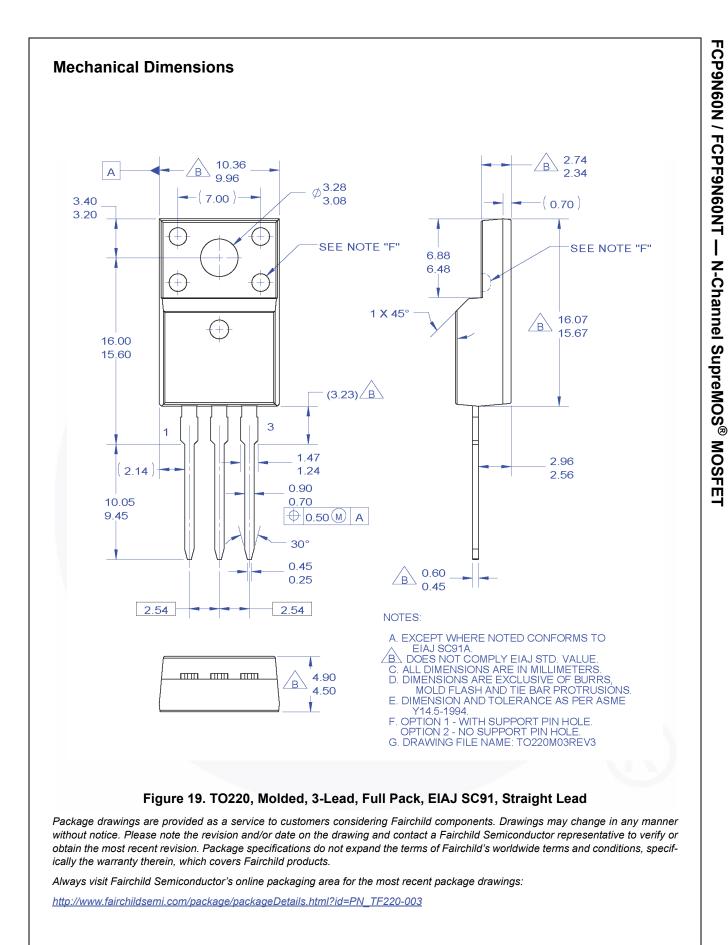




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